

A THRESHOLD VOLTAGE STABILIZER, METHOD OF MANUFACTURING
AND INTEGRATED CIRCUIT EMPLOYING THE SAME

ABSTRACT OF THE DISCLOSURE

The present invention provides a threshold voltage stabilizer for use with a MOS transistor having a body effect associated therewith. In one embodiment, the threshold voltage stabilizer, includes a body well located in a substrate, a source located in the body well, and a stabilization region positioned below the body well. The threshold voltage stabilizer is configured to provide a stabilization voltage to the stabilization region to increase a depletion region within the body well and thereby restrict the body effect to stabilize a threshold voltage of the MOS transistor.